

RJK60S3DPD

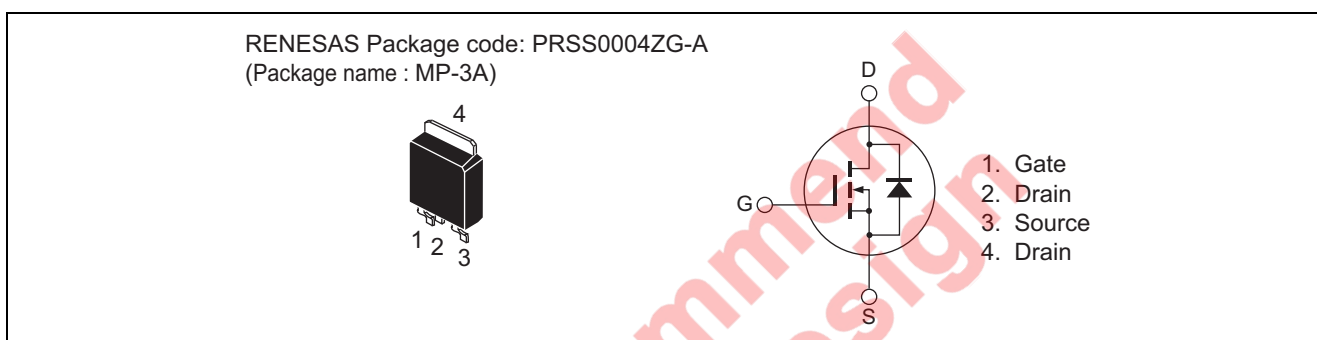
600V - 12A - SJ MOS FET
High Speed Power Switching

R07DS0731EJ0300
Rev.3.00
Oct 12, 2012

Features

- Superjunction MOSFET
- Low on-resistance
 $R_{DS(on)} = 0.35 \Omega$ typ. (at $I_D = 6 A$, $V_{GS} = 10 V$, $T_a = 25^\circ C$)
- High speed switching
 $t_f = 21 ns$ typ. (at $I_D = 6 A$, $V_{GS} = 10 V$, $R_L = 50 \Omega$, $R_g = 10 \Omega$, $T_a = 25^\circ C$)

Outline



Absolute Maximum Ratings

($T_a = 25^\circ C$)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	600	V
Gate to source voltage	V_{GSS}	+30, -20	V
Drain current	$T_c = 25^\circ C$	I_D ^{Note1,2}	12.0
	$T_c = 100^\circ C$	I_D ^{Note1,2}	7.6
Drain peak current	$I_{D(pulse)}$ ^{Note1}	24	A
Body-drain diode reverse drain current	I_{DR} ^{Note1}	12	A
Body-drain diode reverse drain peak current	$I_{DR(pulse)}$ ^{Note1}	24	A
Avalanche current	I_{AP} ^{Note3}	3	A
Avalanche energy	E_{AR} ^{Note3}	0.49	mJ
Channel dissipation	P_{ch} ^{Note4}	73.5	W
Channel to case thermal impedance	θ_{ch-c}	1.7	$^\circ C/W$
Channel temperature	T_{ch}	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

- Notes: 1. Limited by T_{ch} max.
2. Maximum duty cycle $D = 0.75$.
3. $ST_{ch} = 25^\circ C$, $T_{ch} \leq 150^\circ C$
4. Value at $T_c = 25^\circ C$

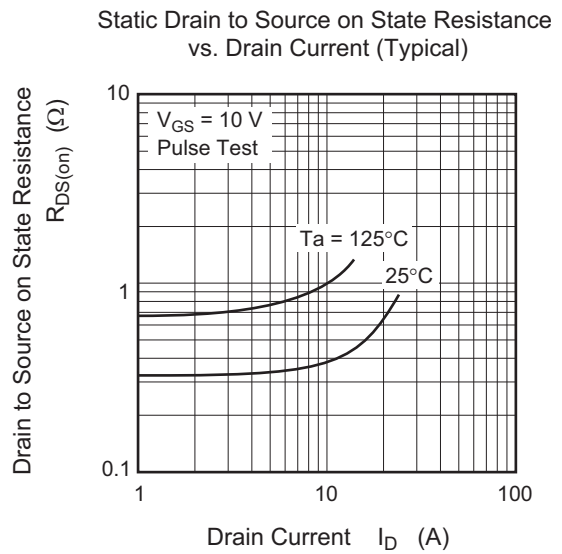
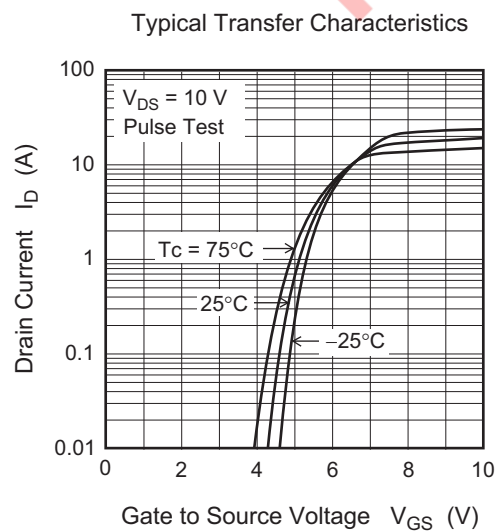
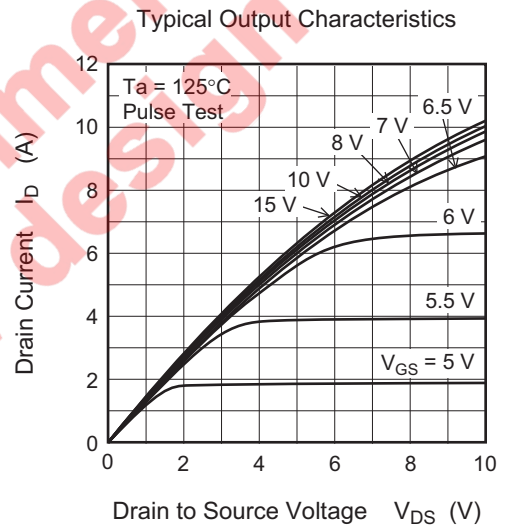
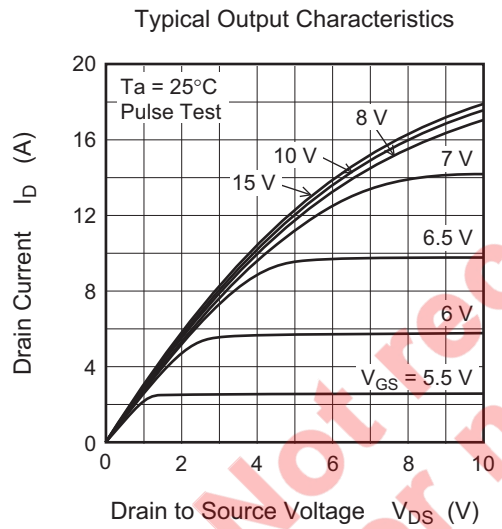
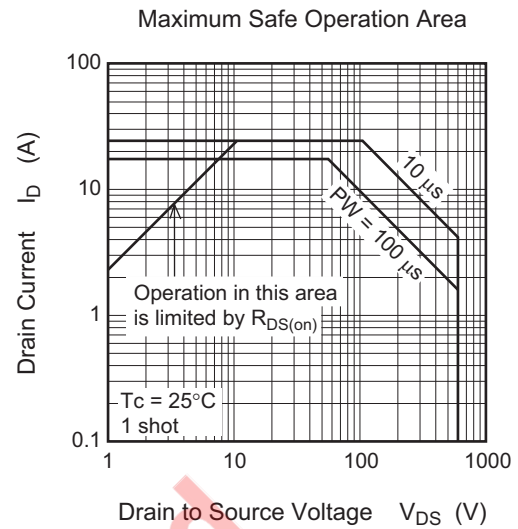
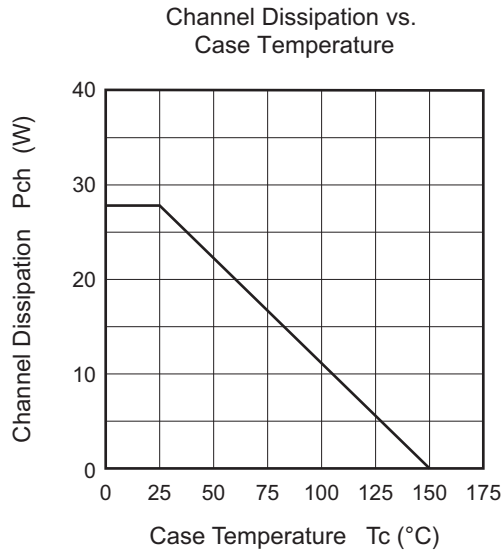
Electrical Characteristics

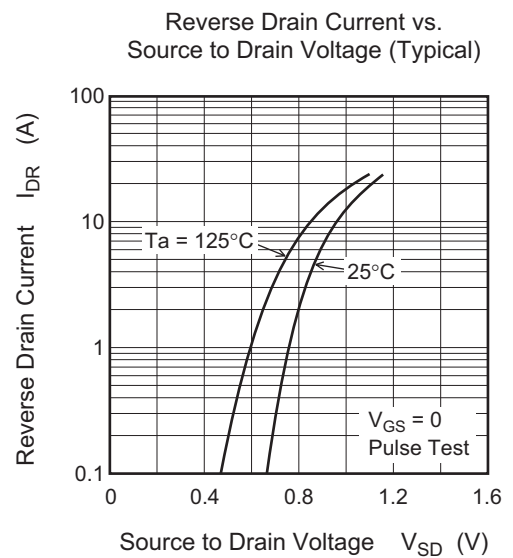
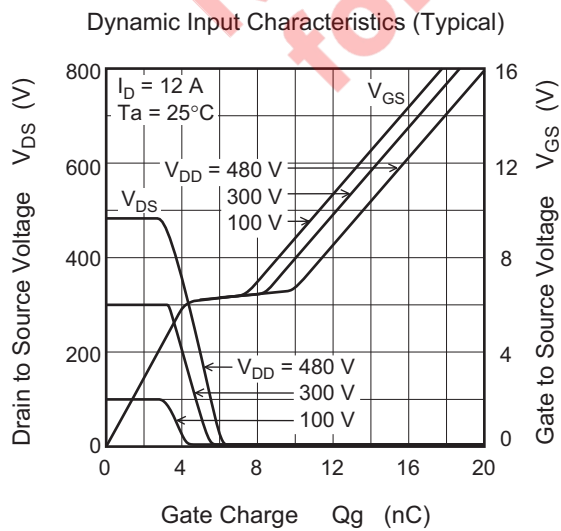
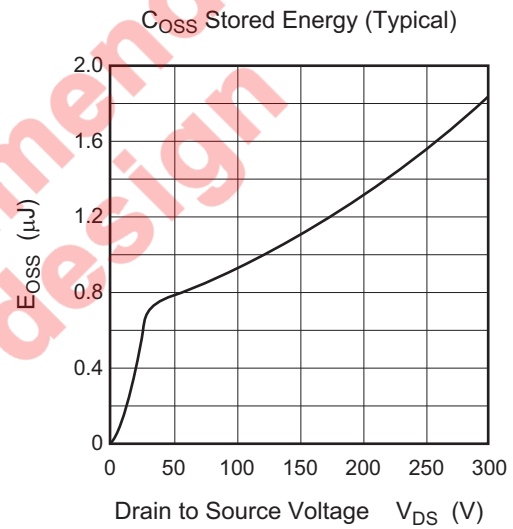
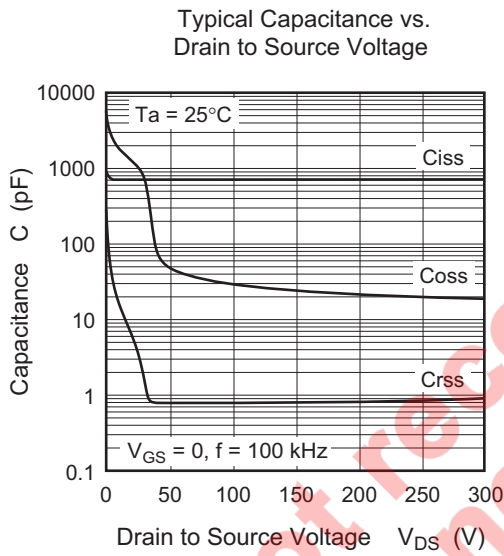
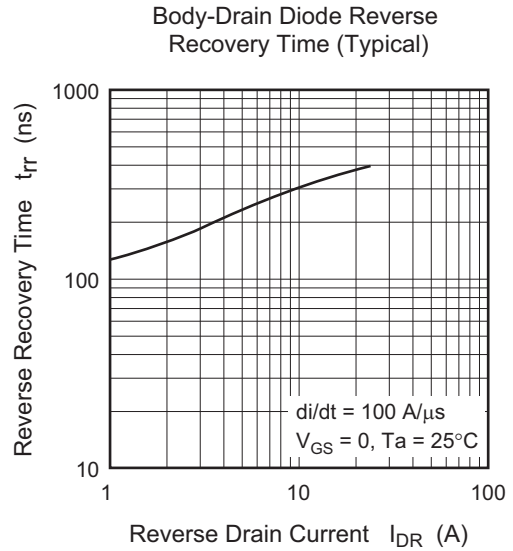
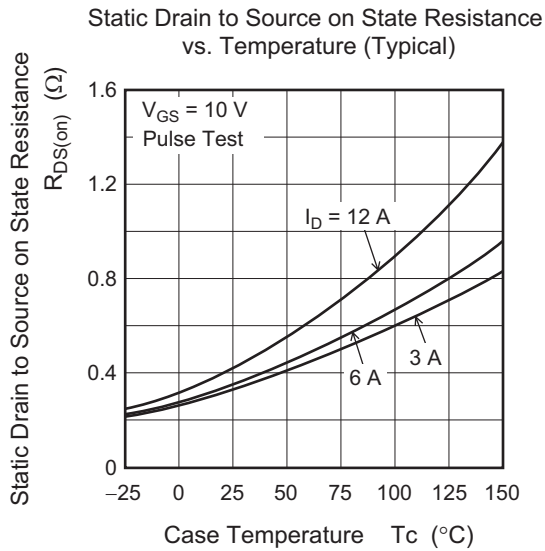
(Ta = 25°C)

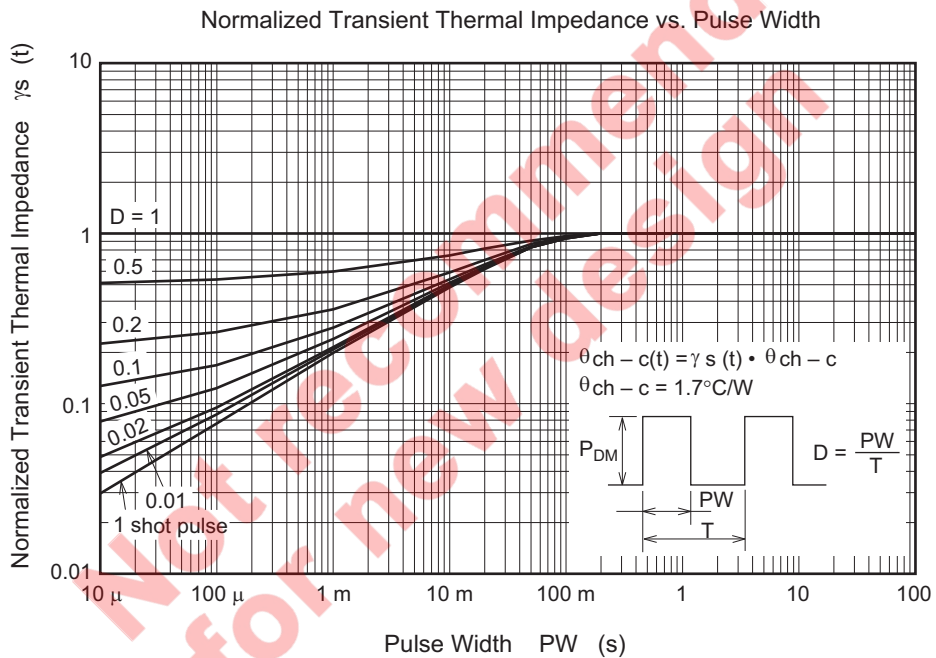
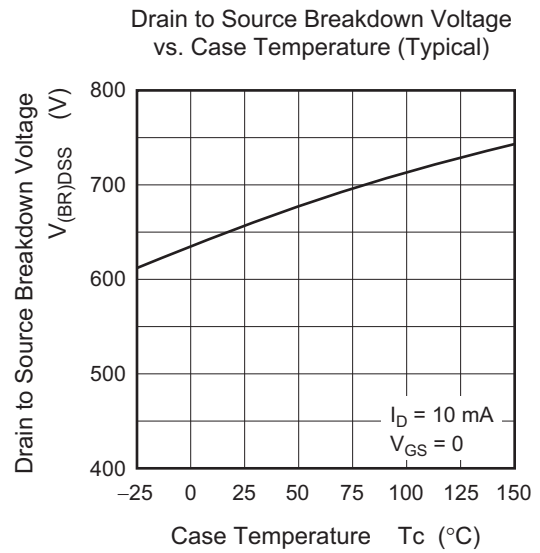
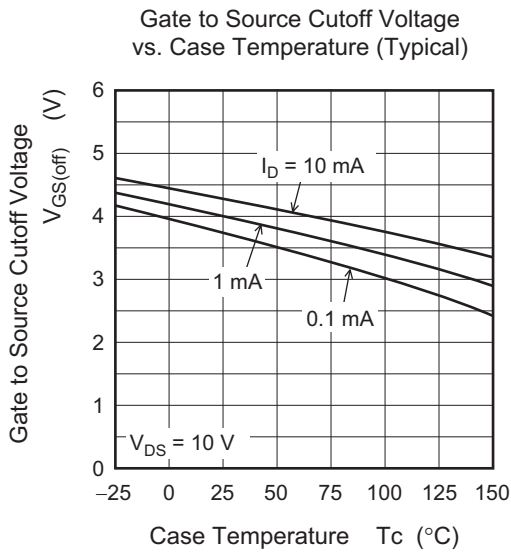
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	600	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	mA	$V_{DS} = 600 \text{ V}$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = +30\text{V}$, -20 V , $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3	—	5	V	$V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.35	0.44	Ω	$I_D = 6 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note5}
	$R_{DS(on)}$	—	0.87	—	Ω	Ta = 150°C $I_D = 6 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note5}
Gate resistance	Rg	—	2.5	—	Ω	f = 1 MHz $V_{DS} = 25 \text{ V}$, $V_{GS} = 0$
Input capacitance	Ciss	—	720	—	pF	$V_{DS} = 25 \text{ V}$
Output capacitance	Coss	—	980	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	—	3.7	—	pF	f = 100 kHz
Turn-on delay time	$t_{d(on)}$	—	13	—	ns	$I_D = 6 \text{ A}$
Rise time	t_r	—	18	—	ns	$V_{GS} = 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	25	—	ns	$R_L = 50 \Omega$
Fall time	t_f	—	18	—	ns	Rg = 10 Ω ^{Note5}
Total gate charge	Qg	—	13.6	—	nC	$V_{DD} = 480 \text{ V}$
Gate to source charge	Qgs	—	4.8	—	nC	$V_{GS} = 10 \text{ V}$
Gate to drain charge	Qgd	—	3.9	—	nC	$I_D = 12 \text{ A}$ ^{Note5}
Body-drain diode forward voltage	V_{DF}	—	1.0	1.6	V	$I_F = 12 \text{ A}$, $V_{GS} = 0$ ^{Note5}
Body-drain diode reverse recovery time	t_{rr}	—	320	—	ns	$I_F = 12 \text{ A}$
Body-drain diode reverse recovery current	I_{rr}	—	20	—	A	$V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$ ^{Note5}
Body-drain diode reverse recovery charge	Q _{rr}	—	3.7	—	μC	

Notes: 5. Pulse test

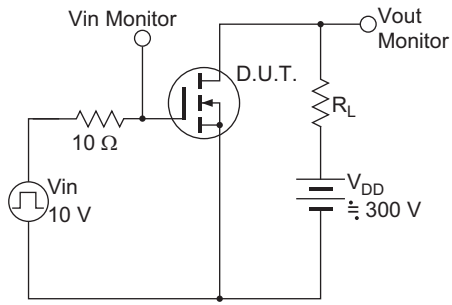
Main Characteristics



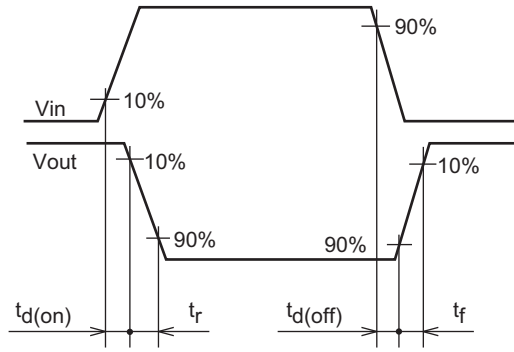




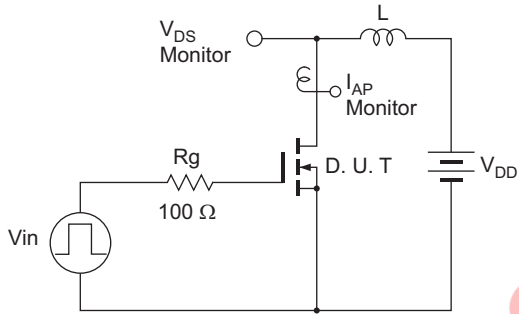
Switching Time Test Circuit



Waveform

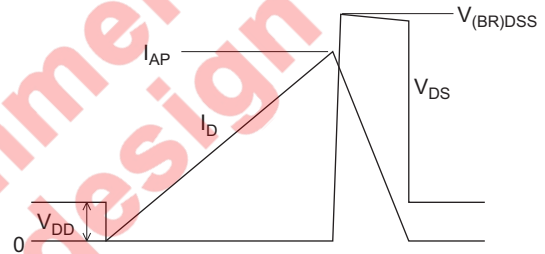


Avalanche Test Circuit



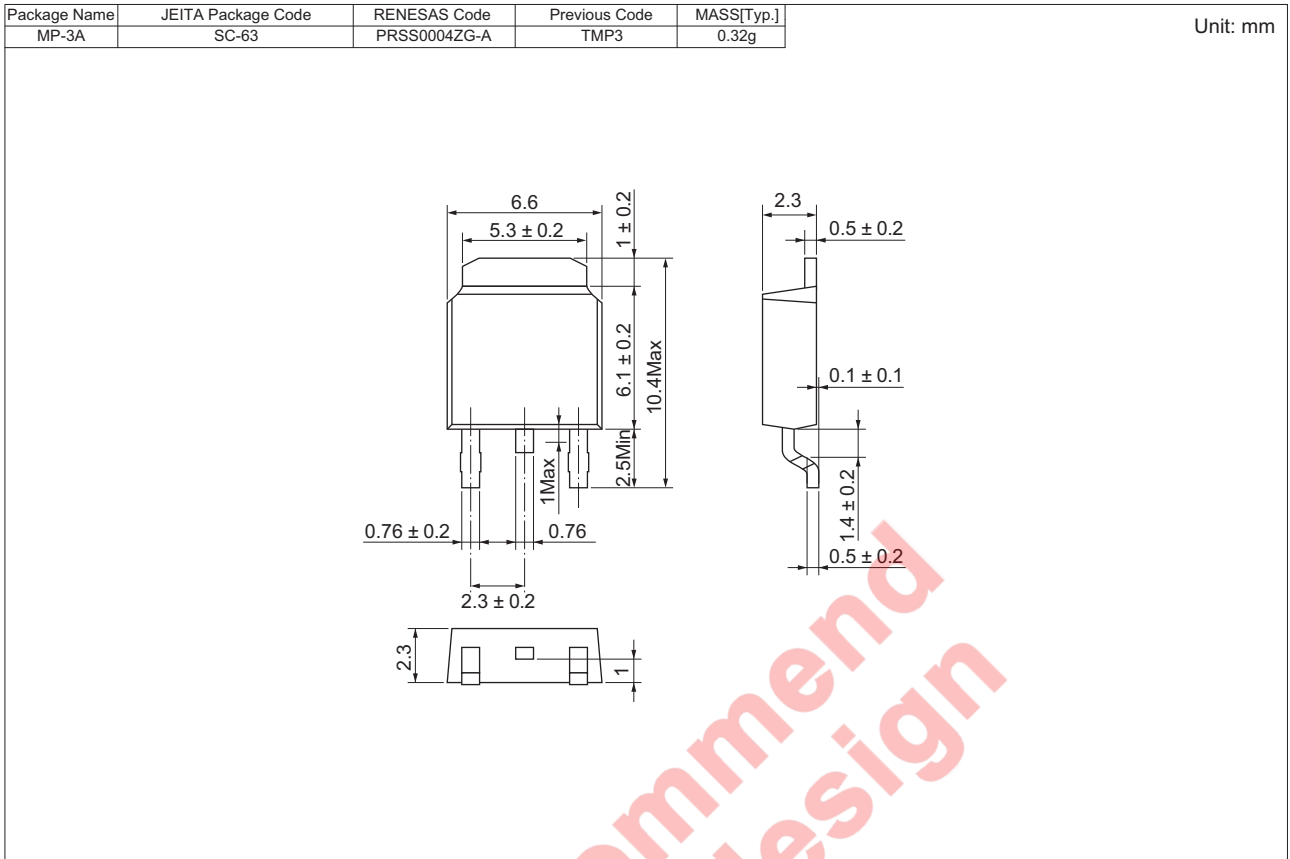
Avalanche Waveform

$$E_{AR} = \frac{1}{2} L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$



Not recommended for new design

Package Dimension



Ordering Information

Orderable Part No.	Quantity	Shipping Container
RJK60S3DPD-00#J2	3000 pcs	Taping

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